



HVEF SERIES

8 to 12kV, 20 to 30mA, 20nS
Axial Lead Low Current Diodes



Features

- Ultra-Fast Reverse Recovery Time
- Miniature Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

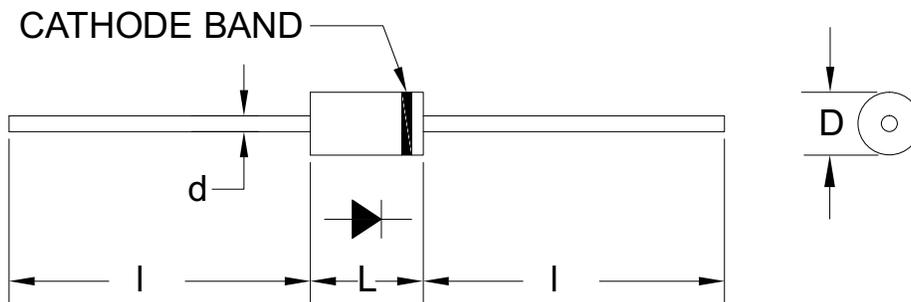
Specifications¹

Part Number	V _{RRM} V	I _{FAVM} mA	V _F V	I _R μA	I _{FSM} A	C _J pF	T _{RR} nS	L in.	D in.	d in.	l in.
HVEF8P	8000	30	20	0.2	3	0.33	20	0.26	0.1	0.021	1.0
HVEF10P	10000	20	23	0.2	3	0.30	20	0.40	0.1	0.021	1.0
HVEF12P	12000	20	27	0.2	3	0.25	20	0.40	0.1	0.021	1.0

Temperature °C	
Operating Temperature	-55 to 125
Storage Temperature	-55 to 175
Maximum Junction Temperature	125

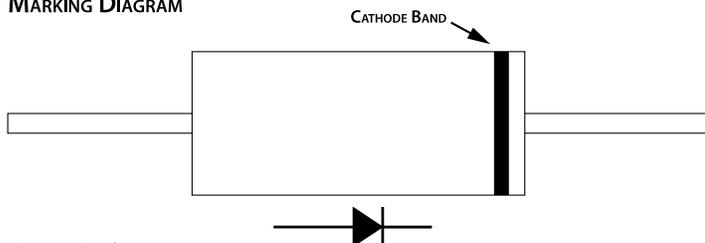
¹125°C ambient temperature unless stated otherwise.

Drawings

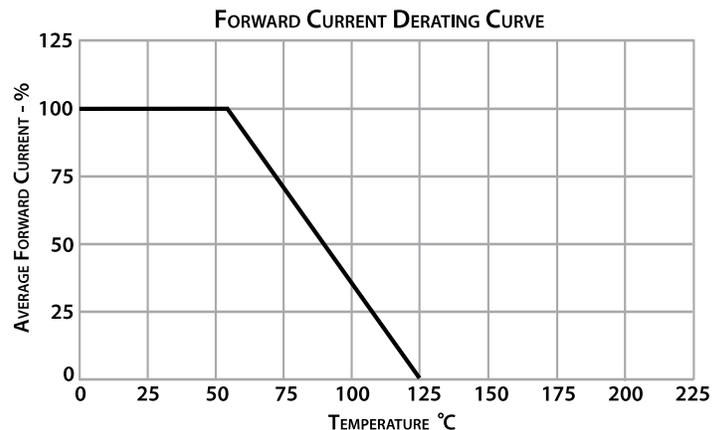


Dimensions in inches, tolerances ±0.020 except as noted

MARKING DIAGRAM



MARKING TYPE: BLUE, INKJET
(MARKINGS WILL WRAP ENTIRE BODY OF DIODE AND ARE SUBJECT TO MINOR CHANGES)





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Specification Definitions

Specifications		Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM}	Maximum Average Forward Current	At T _A = 55°C
V_F	Maximum Forward Voltage Drop	At I _F = 5mA
I_R	Maximum Leakage Current	At V _{RRM}
I_{FSM}	Maximum Surge Current	At 8.3mS, Single Half Sine
C_J	Typical Junction Capacitance	At V _R = 0VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I _F = 2mA; I _R = -4mA; I _{RR} = -1mA

Note: Specifications subject to change without notice. Photo is representation only.